

T-E5YC Low-capacitance bidirectional micro-packaged TVS Diodes for ESD Protection

The T-E5YC is designed with Tech chip Punch-Through process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium. Also because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed, VGA, DVI, SDI and other high speed line applications.

This series has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD(electrostatic discharge), and EFT (electrical fast transients).

Features

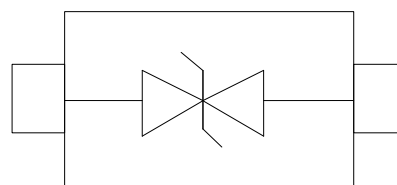
- Peak Power Dissipation — 60 W (8 x 20 us Waveform)
- Stand-off Voltage: 5.0 V
- Replacement for MLV (0603)
- Protects USB2.0、VGA、DVI、HDMI、SDI&I/O Port
- Low Clamping Voltage
- Low Leakage
- Low Capacitance
- Low Body Height: 1.68mm
- Low capacitance (<3.5pF) for high-speed interfaces
- No insertion loss to 2.0GHz
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- ROHS compliant
- **Solid-state Punch-Through TVS Process technology**
- Tech chip technology



SOD-523

Main applications

- High Speed Line :USB1.0/2.0, VGA, DVI, SDI,HDMI
- Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Projection TV
- Cellular handsets and accessories
- Portable instrumentation
- Peripherals



Protection solution to meet

- IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)

Ordering Information

Device	Qty per Reel	Reel Size
T-E5YC	3000	7 Inch

Maximum ratings (Tamb=25°C Unless Otherwise Specified)

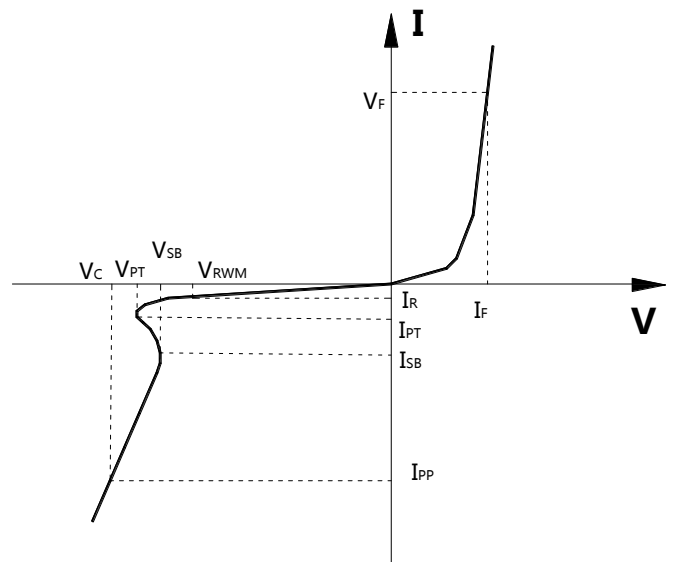
Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20μs waveform)	P _{PPP}	60	Watts
ESD Rating per IEC61000-4-2:			
Contact		8	KV
Air		15	KV
Lead Soldering Temperature	T _L	260 (10 sec.)	°C
Operating Temperature Range	T _J	-55 ~ 150	°C
Storage Temperature Range	T _{STG}	-55 ~ 150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T _L	260	°C

Electrical characteristics (Tamb=25°C Unless Otherwise Specified)

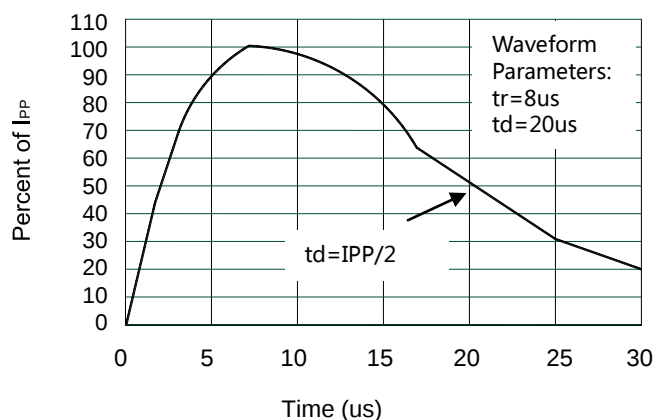
Device	V _{RWM}	I _R @ V _{RWM}	V _{PT} @ 1 mA	V _{SB} @ 50 mA	V _C	Capacitance	
			(Volts)	(Volts)	@ 1 A	@ V _R = 0 V, 1 MHz (pF)	
			Min	Min	(V)	Typ	Max
T-E5YC	5.0	2	6.0	5.3	9.0	2.8	3.5

Junction capacitance is measured in VR=0V,F=1MHz

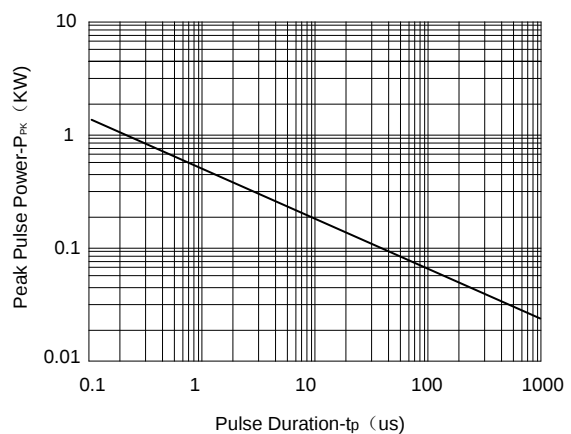
Symbol	Parameter
V _{RWM}	Working Peak Reverse Voltage
V _{PT}	Punch-Through Voltage@ I _{PT}
V _{SB}	Snap-Back Voltage@ I _{SB}
V _C	Clamping Voltage @ I _{PP}
I _T	Test Current
I _{RM}	Leakage current at V _{RWM}
I _{PP}	Peak pulse current
C _O	Off-state Capacitance
C _J	Junction Capacitance



Typical electrical characterist applications

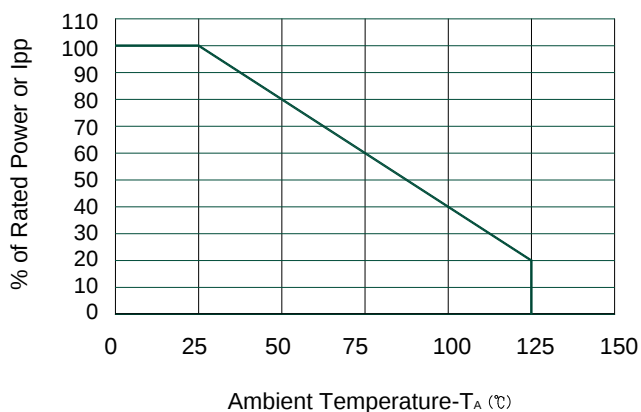


Pulse Waveform

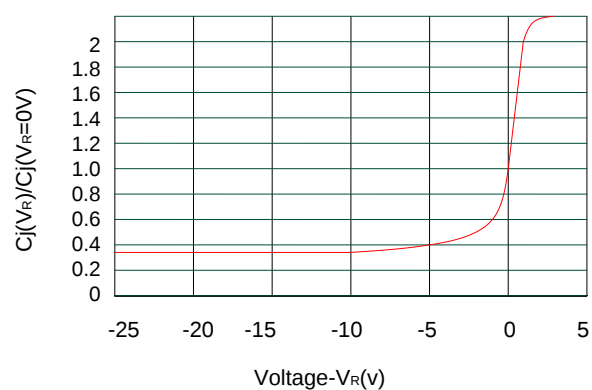


Non-Repetitive Peak Pulse Power vs. Pulse Time

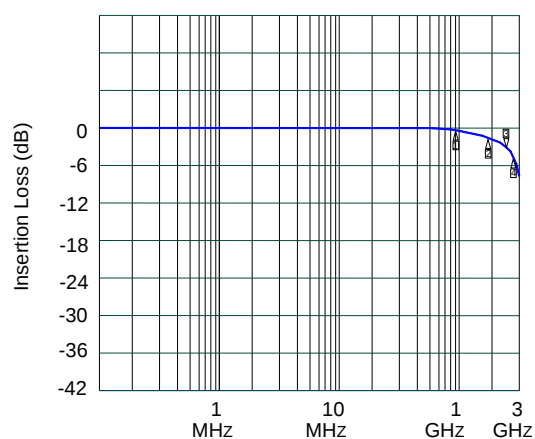
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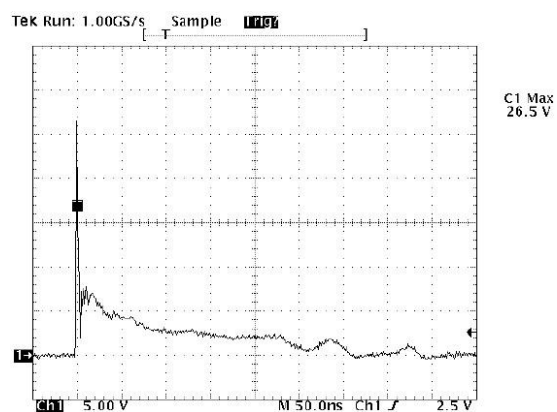
Power Derating Curve



Junction Capacitance vs. Reverse Voltage



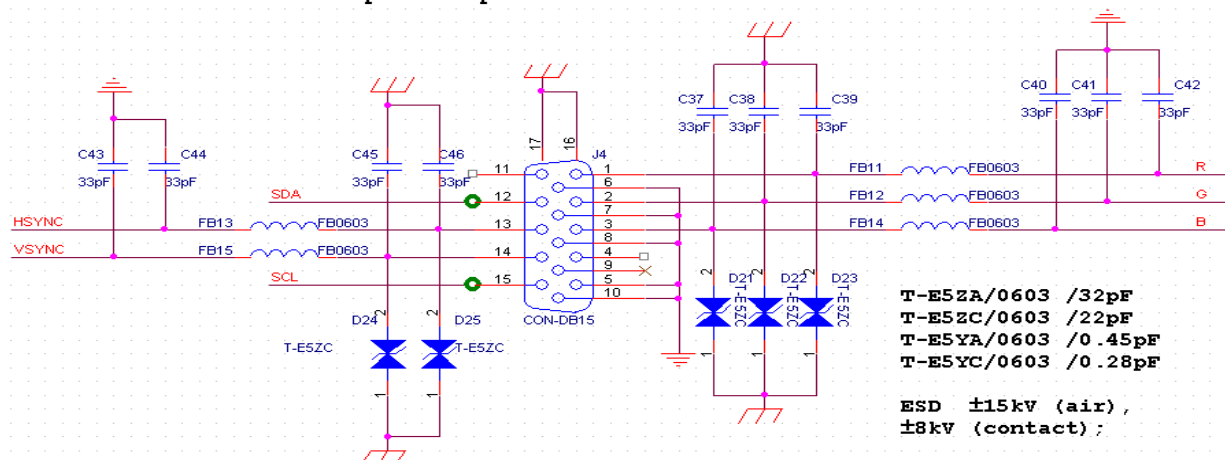
Insertion Loss S21



ESD Response (8kV Contact per IEC 61000-4-2)

Typical applications

Tech Chip VGA protect

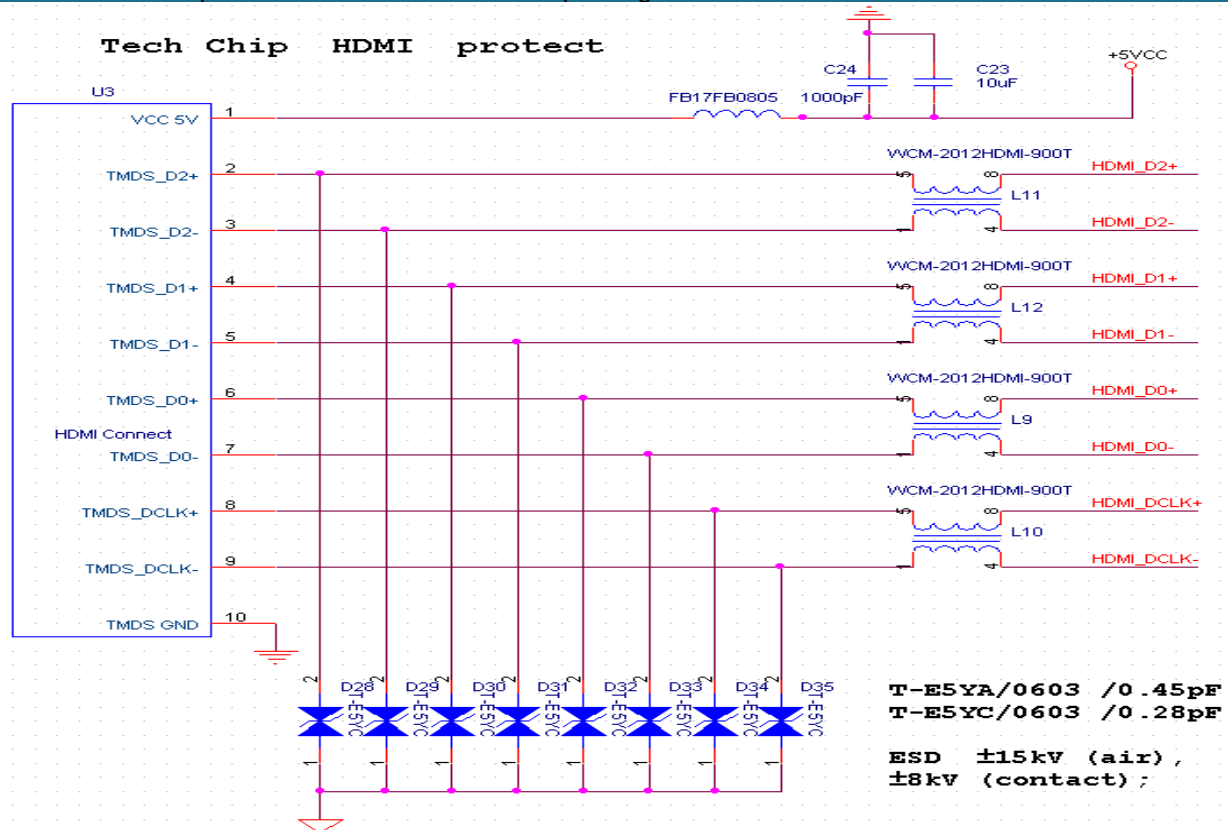


T-E5ZA/0603 /32pF
T-E5ZC/0603 /22pF
T-E5YA/0603 /0.45pF
T-E5YC/0603 /0.28pF

ESD $\pm 15kV$ (air),
 $\pm 8kV$ (contact);

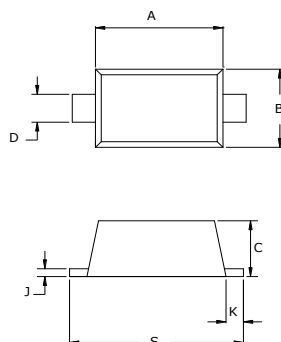
备注:
1、设备为金属外壳时VGA外壳要与PGND直接连接;

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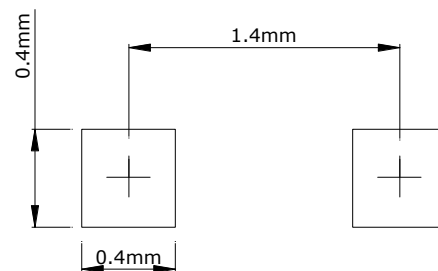


备注:若设备为塑胶外壳无PGND时,TVS接GND处理整;

Package Information (SOD-523)



Recommended Pad outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.10	1.30	0.043	0.051
B	0.70	0.90	0.045	0.053
C	0.50	0.70	0.031	0.043
D	0.25	0.35	0.004	0.012
J	0.07	0.20	0.0028	0.0079
K	0.15	0.25	0.006	0.010
S	1.50	1.70	0.059	0.067